

ABSTRACT OF THE DISCLOSURE

The invention relates to an X-Y address type solid-state image pickup device manufactured by a CMOS process, and has an object to provide an X-Y address type solid-state image pickup device which has a small element size and a wide opening ratio, and can reduce a kTC noise. A photodiode 10, a reset transistor 12, a source follower amplifier 14, and a horizontal selection transistor 16 are formed in each of pixel regions Pmn. A kTC noise reduction circuit 6VR1 for reducing a kTC noise and a CDS circuit 6CL1 are formed outside of the pixel regions Pmn. A differential amplifier is constituted by a first differential transistor 62 of the kTC noise reduction circuit 6VR1 and the source follower amplifier 14 in each of the pixel regions Pmn.

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